

## In the Specification

Page 1, after the Title, please insert the following:

This is a division of US App. No. 09/710,626 filed November 10, 2000 and issued September 9, 2003 as US Pat. No. 6,617,248.

Page 4, paragraph beginning at line 16:

The ruthenium precursor may include a number of materials, including tricarbonyl-1,3-cyclohexadiene ruthenium (referred to herein as "CHDR"), bisethylcyclopentadienylruthenium ( $\text{Ru}(\text{C}_2\text{H}_5\text{C}_5\text{H}_4)_2$ , referred to herein as " $\text{Ru}(\text{EtCp})_2$ "), and ruthenium octanedionate (referred to herein as " $\text{Ru}(\text{OD})_3$ "). The ruthenium precursor is preferably pumped into the chamber at a flow rate of between about 10 sccm to about 2000 sccm, more preferably at a flow rate of between about 100 and about 1000 sccm, and most preferably at a flow rate of about 500 sccm.